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500 W, Unidirectional **Low Capacitance TVS Array**



DESCRIPTION

This Transient Voltage Suppressor (TVS) is assembled in a QFN-143 package which has the same pinout and footprint as the SOT-143 package. The configuration gives protection to 1 unidirectional data or interface line. It is designed for use in applications where low capacitance protection is required at the board level from voltage transients caused by electrostatic discharge (ESD) as defined in IEC 61000-4-2, electrical fast transients (EFT) per IEC 61000-4-4 and the secondary effects of lightning. These TVS arrays have a peak power rating of 500 watts for an 8/20 µs pulse (figure 1). With a capacitance of only 3 pF, this part can provide protection to very fast data lines including USB at 900 Mbits/sec.





QFN-143

Important: For the latest information, visit our website http://www.microsemi.com.

FEATURES

- Protects 1 unidirectional line
- Surge protection per IEC 61000-4-2 and IEC 61000-4-4
- Ultra low capacitance
- Low profile surface mount package
- RoHS compliant

Also available:

Bidirectional

APPLICATIONS / BENEFITS

EIA RS485 data rates: 5 Mbps

10 Base-T Ethernet

USB data rate 900 Mbps

(QFN-143) USBQ50403Ce3 USBQ50424Ce3

MAXIMUM RATINGS @ 25 °C unless otherwise noted

Parameters/Test Conditions	Symbol	Value	Unit
Storage Temperature	T _{STG}	-55 to +150	°C
Junction Temperature	TJ	-55 to +125	°C
Peak Pulse Power Dissipation with a 8/20µs waveform (with a duty factor of 0.01%)	P _{PP}	500	W
Solder Temperature @ 10 s		260	°C

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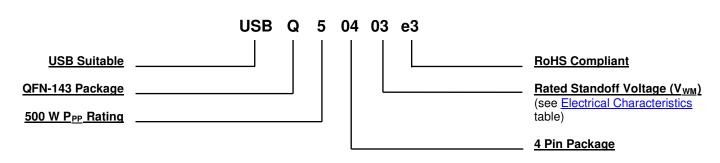
www.microsemi.com



MECHANICAL and PACKAGING

- CASE: Void-free transfer molded thermosetting epoxy body meeting UL94V-0.
- TERMINALS: RoHS compliant annealed matte-tin plating. Readily solderable per MIL-STD-750, method 2026.
- MARKING: Body marked with part number code (Qxx).
- POLARITY: Dot in corner indicates pin 1.
- TAPE-AND-REEL: Standard per EIA-481-B (add "TR" suffix to part number). Consult factory for quantities.
- Approximately 16.53 milligrams
- See <u>Package Dimensions</u> on last page.

PART NOMENCLATURE



	SYMBOLS & DEFINITIONS				
Symbol	Definition				
$\alpha_{V(BR)}$	Temperature Coefficient of Breakdown Voltage: The change in breakdown voltage divided by the change in temperature that caused it expressed in %/°C or mV/°C.				
I _(BR)	Breakdown Current: The current used for measuring Breakdown Voltage V _{(BR).}				
I _D	Standby Current: The current through the device at rated stand-off voltage.				
I _{PP}	Peak Impulse Current: The maximum rated random recurring peak impulse current or nonrepetitive peak impulse current that may be applied to a device. A random recurring or nonrepetitive transient current is usually due to an external cause, and it is assumed that its effect will have completely disappeared before the next transient arrives.				
$V_{(BR)}$	Breakdown Voltage: The voltage across the device at a specified current I _(BR) in the breakdown region.				
V _C	Clamping Voltage: The voltage across the device in a region of low differential resistance during the application of an impulse current (I _{PP}) for a specified waveform.				
V _{WM}	Working Standoff Voltage: The maximum-rated value of dc or repetitive peak positive cathode-to-anode voltage that may be continuously applied over the standard operating temperature.				

ELECTRICAL CHARACTERISTICS @ 25 °C unless otherwise stated

PART NUMBER	DEVICE MARKING	STAND- OFF VOLTAGE V _{WM} Volts	BREAKDOWN VOLTAGE V _{BR} @ 1 mA Volts	CLAMPING VOLTAGE V _C @ 1 Amp (Figure 2) Volts	CLAMPING VOLTAGE V _C @ 5 Amp (Figure 2) Volts	STANDBY CURRENT I _D @ V _{WM} µA MAX	CAPACITANCE (f= 1 MHz) C @ 0 V pF	TEMPERATURE COEFFICIENT OF V _{BR} α _{VBR} mV/°C
USBQ50403e3	Q03	3.3	4.0	8.0	11	200	3	-5
USBQ50405e3	Q05	5.0	6.0	10.8	12	40	3	1
USBQ50412e3	Q12	12.0	13.3	19.0	26	1	3	8
USBQ50415e3	Q15	15.0	16.7	24.0	32	1	3	11
USBQ50424e3	Q24	24.0	26.7	43.0	57	1	3	28



GRAPHS

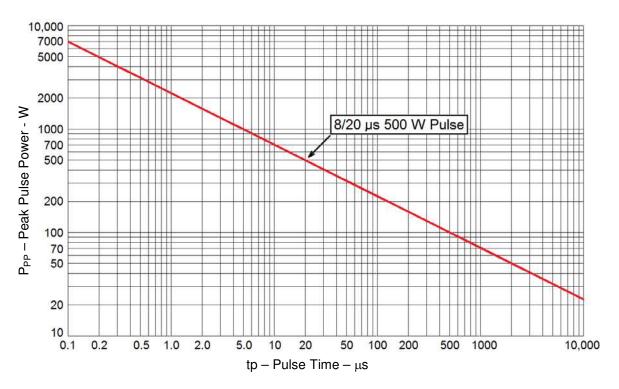


FIGURE 1
Peak Pulse Power vs. Pulse Time

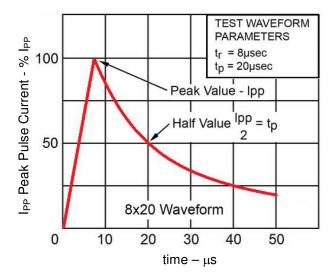
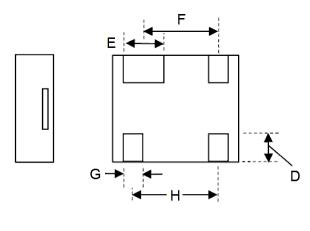
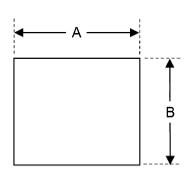


FIGURE 2
Pulse Waveform



PACKAGE DIMENSIONS

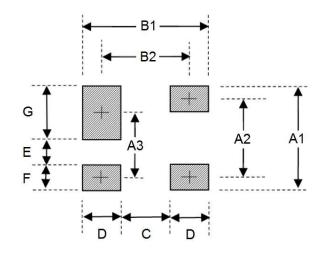






	Dimensions					
Ref.	lr	nch	Millimeters			
	Min	Max	Min	Max		
Α	0.112	0.116	2.85	2.95		
В	0.096	0.100	2.45	2.55		
С	0.0354	0.0366	0.900	0.930		
D	0.020	0.024	0.50	0.60		
Е	0.031	NOM	0.80	NOM		
F	0.069	NOM (1.75	NOM		
G	0.018	NOM	0.45	NOM		
Н	0.076	NOM	1.92	NOM		

PAD LAYOUT

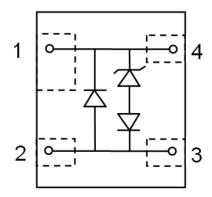


	Dime	ensions		
Ref.	Inch	Millimeters		
	Nominal	Nominal		
A 1	0.112	2.85		
A2	0.079	2.00		
A 3	0.071	1.80		
B1	0.108	2.75		
B2	0.075	1.90		
O	0.041	1.05		
D	0.033	0.85		
Е	0.032	0.80		
F	0.033	0.85		
G	0.047	1.20		

See schematic on next page



SCHEMATIC



Seen from above